# AIP3D15A060Q4(N) AIP3P15A060Q4(N)

## Dual-In-Line Package Intelligent Power Module

#### **External View**



Size: 38 x 24 x 3.6 mm



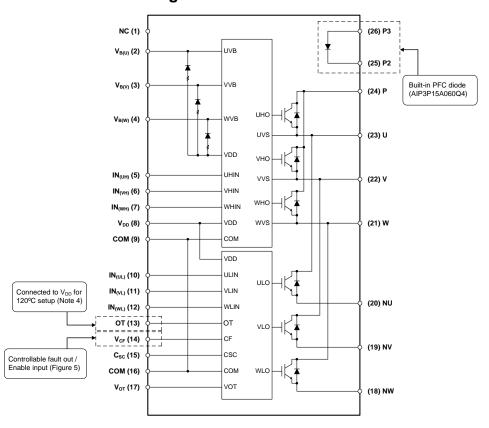
#### **Features**

- UL Recognized: UL 1775 File E345245
- 3-phase inverter module with optional built-in PFC diode
- 600V-15A (Trench Shielded Planar Gate IGBT)
- Low V<sub>F</sub> and Ultra-fast recovery diode for PFC (AIP3P15A060Q4)
- Built-in bootstrap diodes with integrated current-limiting resistor
- Control supply under-voltage lockout protection (UVLO)
- Controllable over-temperature protection (OT)
- Temperature monitoring (V<sub>OT</sub>)
- Short-circuit current protection (C<sub>SC</sub>)
- Controllable fault out signal (V<sub>CF</sub>) corresponding to SC, UV and OT fault
- Enable input functionality: Low-side IGBTs shut-down
- Input interface: 3 and 5V line, Schmitt trigger receiver circuit (Active high)
- Isolation ratings of 2000Vrms/min

## **Applications**

- AC 100-240Vrms class low power motor drives
- Air-conditioners, Washing machines, Compressors and Fan Motors

## **Internal Equivalent Circuit / Pin Configuration**





## **Ordering Information**

Part Number	Temperature Range	Package	Terminal type
AIP3D15A060Q4	-40°C to 150°C	IPM-3	Long
AIP3D15A060Q4N	-40°C to 150°C	IPM-3A	Normal
AIP3P15A060Q4	-40°C to 150°C	IPM-3B	Long with PFC diode
AIP3P15A060Q4N	-40°C to 150°C	IPM-3C	Normal with PFC diode



AOS Green Products use reduced levels of Halogens, and are also RoHS compliant. Please visit www.aosmd.com/media/AOSGreenPolicy.pdf for additional information.

## **Pin Description**

Pin Number	Pin Name	Pin Function
1	NC	No Connection
2	$V_{B(U)}$	High-Side Bias Voltage for U-Phase IGBT Driving
3	$V_{B(V)}$	High-Side Bias Voltage for V-Phase IGBT Driving
4	$V_{B(W)}$	High-Side Bias Voltage for W-Phase IGBT Driving
5	IN <sub>(UH)</sub>	Signal Input for High-Side U-Phase
6	IN <sub>(VH)</sub>	Signal Input for High-Side V-Phase
7	IN <sub>(WH)</sub>	Signal Input for High-Side W-Phase
8	$V_{DD}$	Common Bias Voltage for IC and IGBTs Driving
9	СОМ	Common Supply Ground
10	IN <sub>(UL)</sub>	Signal Input for Low-Side U-Phase
11	IN <sub>(VL)</sub>	Signal Input for Low-Side V-Phase
12	IN <sub>(WL)</sub>	Signal Input for Low-Side W-Phase
13	OT	Controllable Over Temperature Protection (Connected to V <sub>DD</sub> for 120°C setup)
14	$V_{CF}$	Controllable Fault Output
15	C <sub>SC</sub>	Capacitor (Low-Pass Filter) for Short-circuit Current Detection Input
16	COM	Common Supply Ground
17	V <sub>OT</sub>	Voltage Output of LVIC Temperature
18	NW	Negative DC-Link Input for W-Phase
19	NV	Negative DC-Link Input for V-Phase
20	NU	Negative DC-Link Input for U-Phase
21	W	Output for W-Phase
22	V	Output for V-Phase
23	U	Output for U-Phase
24	Р	Positive DC-Link Input
25	P2	PFC Diode Cathode (AIP3P15A060Q4)
26	P3	PFC Diode Anode (AIP3P15A060Q4)

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## **Absolute Maximum Ratings**

 $T_J = 25$ °C, unless otherwise specified.

Symbol	Parameter	Conditions	Ratings	Units
Inverter				
$V_{PN}$	Supply Voltage	Applied between P - NU,NV,NW	450	V
V <sub>PN(surge)</sub>	Supply Voltage (surge)	Applied between P - NU,NV,NW	500	V
V <sub>CES</sub>	Collector-Emitter Voltage		600	V
	Outside Disease Outside	T <sub>C</sub> =25°C, T <sub>J</sub> <150°C	15	А
I <sub>C</sub>	Output Phase Current	T <sub>C</sub> =80°C, T <sub>J</sub> <150°C	10	А
±l <sub>PK</sub>	Output Peak Phase Current	T <sub>C</sub> =25°C, less than 1ms pulse width	30	А
t <sub>SC</sub>	Short Circuit Withstand Time	V <sub>PN</sub> ≤400V, T <sub>J</sub> =150°C, V <sub>DD</sub> =15V	5	μs
Pc	Collector Dissipation	T <sub>C</sub> =25°C, per chip	33	W
TJ	Operating Junction Temperature		-40 to 150	°C
PFC Diode	•			
$V_{RRM}$	Repetitive peak Reverse Voltage	Applied between P2 – P3	650	V
		T <sub>C</sub> =25°C, T <sub>J</sub> <150°C	30	А
I <sub>F</sub>	Output Phase Current	T <sub>C</sub> =100°C, T <sub>J</sub> <150°C	15	А
Control (P	rotection)			
$V_{DD}$	Control Supply Voltage	Applied between V <sub>DD</sub> -COM	25	V
$V_{DB}$	High-Side Control Bias Voltage	Applied between V <sub>B(U)</sub> -U, V <sub>B(V)</sub> -V, V <sub>B(W)</sub> -W	25	V
V <sub>IN</sub>	Input Voltage	Applied between IN <sub>(UH)</sub> , IN <sub>(VH)</sub> , IN <sub>(WH)</sub> , IN <sub>(UL)</sub> , IN <sub>(VL)</sub> , IN <sub>(WL)</sub> – COM	V <sub>DD</sub> +0.3	V
V <sub>CF</sub>	Fault Output Supply Voltage	Applied between V <sub>CF</sub> -COM	COM+5.5	V
I <sub>CF</sub>	Fault Output Current	Sink current at V <sub>CF</sub> terminal	1	mA
V <sub>SC</sub>	Current Sensing Input Voltage	Applied between C <sub>SC</sub> -COM	COM+5.5	V
V <sub>OT</sub>	Temperature Output	Applied between V <sub>OT</sub> -COM	COM+5.5	V
Total Syst	em			
V <sub>PN(PROT)</sub>	Self Protection Supply Voltage Limit (Short-Circuit Protection Capability)	V <sub>DD</sub> =13.5-16.5V, Inverter part T <sub>J</sub> =150°C, Non-repetitive, less than 2µs	400	V
T <sub>C</sub>	Module Case Operation Temperature	Measurement point of T <sub>C</sub> is provided in Figure 1	-30 to 125	°C
T <sub>STG</sub>	Storage Temperature		-40 to 150	°C
V <sub>ISO</sub>	Isolation Voltage	60Hz, sinusoidal, AC 1min, between connected all pins and heat sink plate	2000	V <sub>rms</sub>

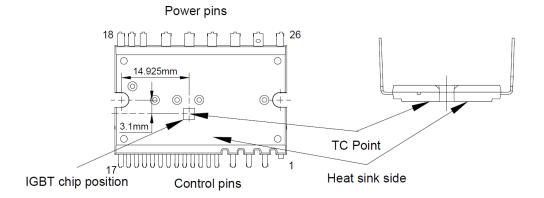


Figure 1. T<sub>C</sub> Measurement Point

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## **Thermal Resistance**

Symbol	Parameter	Conditions	Min.	Тур.	Max.	Units
R <sub>th(j-c)Q</sub>	Junction to Case Thermal Resistance (1)	Inverter IGBT (per 1/6 module)	-	1	3.8	K/W
R <sub>th(j-c)F</sub>		Inverter FWD (per 1/6 module)	-	ı	4.97	K/W
$R_{th(j-c)D}$		PFC Diode (AIP3P15A060Q4)	-	-	2.58	K/W

#### Note:

#### **Electrical Characteristics**

 $T_J = 25$ °C, unless otherwise specified.

Symbol	Parameter	Conditions		Min.	Тур.	Max.	Units	
Inverter								
1/	Collector-Emitter Saturation	V <sub>DD</sub> =V <sub>DB</sub> =15V,	I <sub>C</sub> =7.5A, T <sub>J=</sub> 25°C	-	1.40	1.90	V	
$V_{CE(SAT)}$	Voltage	V <sub>IN</sub> =5V	I <sub>C=7.5</sub> A, T <sub>J</sub> =125°C	-	1.60	-	V	
$V_{F}$	FWD Forward Voltage	V <sub>IN</sub> =0	I <sub>F</sub> =7.5A, T <sub>J</sub> =25°C	-	1.55	2.00	V	
ton				0.40	0.70	1.20	μs	
t <sub>C(ON)</sub>		$V_{PN}$ =300V, $V_{DD}$ = $V_{DB}$ =	=15V	-	0.15	0.40	μs	
$t_{OFF}$	Switching Times	I <sub>C</sub> =10A, T <sub>J</sub> =25°C, V <sub>IN</sub>	$_{N}$ =0V $\leftrightarrow$ 5V	-	1.25	1.75	μs	
$t_{C(OFF)}$		Inductive load		-	0.10	0.30	μs	
t <sub>rr</sub>				-	0.10	-	μs	
I <sub>CES</sub>	Collector-Emitter Leakage	Vc=Vc=s	T <sub>J</sub> =25°C	-	-	1	mA	
ICES	Current	V CE – V CES	T <sub>J</sub> =125°C	-	-	10	mA	
PFC Diode								
$V_{F}$	FWD Forward Voltage		I <sub>F</sub> =20A, T <sub>J</sub> =25°C	-	1.45	-	V	
T <sub>rr</sub>	Reverse recovery time				90		ns	
$Q_{rr}$	Reverse recovery Charge	T = 25°C V = 400V	T <sub>J</sub> =25°C, V <sub>R</sub> =400V, I <sub>F</sub> =20A, dI <sub>F</sub> /dt=320A/us				uC	
Irr	Peak reverse recovery current	15-20 G, VR-100 V,	r-2011, dir/di-02011 do		10.7		А	
Control (P	rotection)							
$I_{QDD}$	Quiescent V <sub>DD</sub> Supply Current	V <sub>DD</sub> =15V, IN <sub>(UH,VH,WH,UL,VL,WL)</sub> =0V	V <sub>DD</sub> -COM	-	-	2.1	mA	
I <sub>QDB</sub>	Quiescent V <sub>DB</sub> Supply Current	V <sub>DB</sub> =15V, IN <sub>(UH, VH, WH)</sub> =0V	$V_{B(U)}\text{-}U,V_{B(V)}\text{-}V,V_{B(W)}\text{-}W$	-	-	0.3	mA	
$V_{\text{SC(ref)}}$	Short-Circuit Trip Level	V <sub>DD</sub> =15V (2)		0.455	0.48	0.505	V	
$UV_{DT}$		Trip Level		10.3	11.4	12.5	V	
$UV_DR$	Supply Circuit Under-Voltage	Reset Level		10.8	11.9	13.0	V	
$UV_DBT$	Protection	Trip Level		8.5	9.5	10.5	V	
$UV_DBR$		Reset Level		9.5	10.5	11.5	V	
\ <u></u>	Temperature Output (3)		LVIC Temperature=90°C	2.67	2.77	2.86	V	
V <sub>OT</sub>	Temperature Output		LVIC Temperature=25°C	8.0	1.05	1.3	V	
OT <sub>T</sub>	Over-Temperature	The OT Pin is	Trip Level	100	120	140	°C	
OT <sub>HYS</sub>	Protection (4)	connected to V <sub>DD</sub> or open	Hysteresis of Trip Reset	-	30	-	°C	

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<sup>1.</sup> For the measurement point of case temperature  $(T_{\mathbb{C}})$ , please refer to Figure 1.



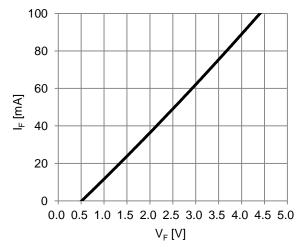
Symbol	Parameter	Conditions	Min.	Тур.	Max.	Units		
Control (P	Control (Protection)							
$V_{CFH}$	Foult Output Valtage	V <sub>SC</sub> =0V, V <sub>CF</sub> Circuit: 10kΩ to 5V pull-up	4.9	-	-	V		
$V_{CFL}$	Fault Output Voltage	V <sub>SC</sub> =1V, V <sub>CF</sub> Circuit: 10kΩ to 5V pull-up	-	-	0.5	V		
V <sub>CF+</sub>	CF positive going threshold		-	1.9	2.2	V		
V <sub>CF</sub> -	CF negative going threshold		0.8	1.1	-	V		
	Fault Output Pulse Width (5)	Pull-up resistor only	20	-	-	μs		
t <sub>FO</sub>		Pull-up resistor with pull-down capacitor ( $R_{CF}$ =2.2 $M\Omega$ , $C_{CF}$ =1 $nF$ , 5 $V$ pull-up) (Figure 5)	-	1	-	ms		
I <sub>IN</sub>	Input Current	V <sub>IN</sub> =5V	-	0.72	-	mA		
V <sub>th(on)</sub>	ON Threshold Voltage			2.3	2.6	V		
V <sub>th(off)</sub>	OFF Threshold Voltage	Applied between IN <sub>(UH)</sub> , IN <sub>(VH)</sub> , IN <sub>(WH)</sub> , IN <sub>(UL)</sub> ,	0.8	1.2		V		
V <sub>th(hys)</sub>	ON/OFF Threshold Hysteresis Voltage	IN <sub>(VL)</sub> , IN <sub>(WL)</sub> -COM	-	1.1	-	V		
V <sub>F(BSD)</sub>	Bootstrap Diode Forward Voltage	I <sub>F</sub> =10mA Including Voltage Drop by Limiting Resistor <sup>(6)</sup>	0.5	1.0	1.5	V		
R <sub>BSD</sub>	Built-in Limiting Resistance	Included in Bootstrap Diode	80	100	120	Ω		

#### Notes:

- 2. Short-circuit protection works only for low sides.
- When temperature exceeds the protective level that the user defined, the controller (MCU) should stop the IPM. Temperature of LVIC vs. V<sub>OT</sub> output characteristics is described in Figure 3.
- When the LVIC temperature exceeds OT Trip temperature level (OT<sub>T</sub>), OT protection is triggered and fault outputs. OT Trip level can be adjusted by pull-down resistors values as shown in the table below.

OT Pin	OT <sub>⊤</sub> [°C]
10kΩ	Disable
100kΩ	130
400kΩ	110
V <sub>DD</sub> or Open	120

- Fault signal (F<sub>O</sub>) outputs when SC, UV or OT protection is triggered. F<sub>O</sub> pulse width is different for each protection mode. At SC failure, F<sub>O</sub> pulse width is fixed (minimum 20μs) or controlled by RC network (see Figure 5), but at UV or OT failure, F<sub>O</sub> outputs continuously until recovering from UV or OT state.
- 6. The characteristics of bootstrap diodes are shown in Figure 2.



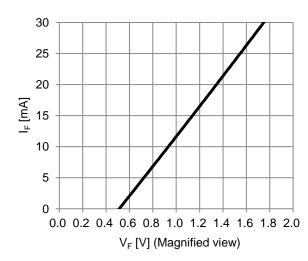


Figure 2. Built-in Bootstrap Diode V<sub>F</sub>-I<sub>F</sub> Characteristic (T<sub>C</sub>=25°C)

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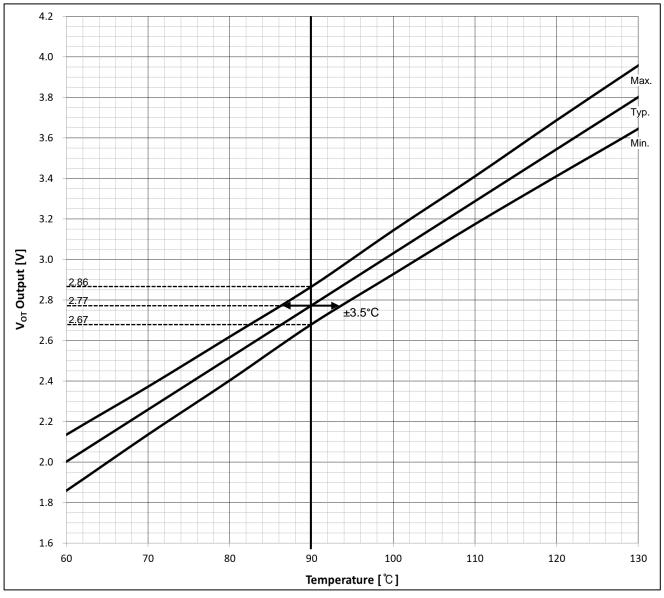
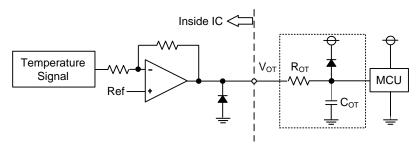


Figure 3. Temperature of LVIC vs. VoT Output Characteristics

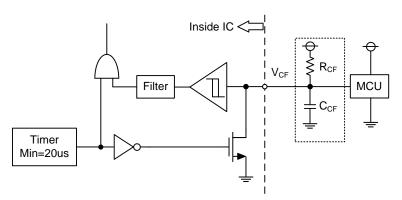


- (1) In the case of using  $V_{OT}$  with low voltage controller like 3.3V MCU,  $V_{OT}$  output might exceed control supply voltage 3.3V when temperature rises excessively. If system uses low voltage controller, it is recommended to insert a clamp diode between control supply of the controller and  $V_{OT}$  output for preventing over voltage destruction.
- (2) When  $V_{OT}$  is connected to MCU, to use RC ( $R_{OT}$ =2 $k\Omega$ ,  $C_{OT}$ =10nF) filter is recommended.
- (3) In the case of not using  $V_{\text{OT}}$ , leave  $V_{\text{OT}}$  output NC (No connection).

Figure 4. Interface Circuit at Pin Vot

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- (1) The V<sub>CF</sub> pin combines three functions in one pin: Fixed fault out, Controllable fault out pulse width based on RC network, and Enable input.
- (2) The V<sub>CF</sub> pin provides an enable functionality that allows it to shut down the all low-side IGBTs. When the V<sub>CF</sub> pin is in the high state the IPM is able to operate normally. If the V<sub>CF</sub> pin is in a low state, the low-side IGBTs are turned off until the enable condition is restored. In addition, the V<sub>CF</sub> pin can provide the fault output signal with the fixed or controlled fault out pulse width.
- (3) If a pull-up resistor (10kΩ) only is connected to the V<sub>CF</sub> pin, the fault output pulse width is fixed at minimum 20us.
- (4) If a capacitor (C<sub>CF</sub>) is connected with a pull-up resistor (R<sub>CF</sub>) together, the fault output pulse width can be controlled according to the resistor and the capacitor values. The length of fault output pulse width is determined by the following formula;
  - $t_{FO} = -(R_{CF} * C_{CF}) * ln(1 V_{CF} + / V_{DD}) + 100 ns + 20 us(min.)$
  - ex)  $V_{DD}=5V$ ,  $R_{CF}=2.2M\Omega$ ,  $C_{CF}=1nF$ ,  $t_{FO}\approx1.07ms$ . Recommended parameters in the design are  $C_{CF}$  of  $\leq 1nF$  and  $R_{CF}$  of 0.1M to 2.2M $\Omega$ .

Figure 5. Interface Circuit at Pin V<sub>CF</sub>

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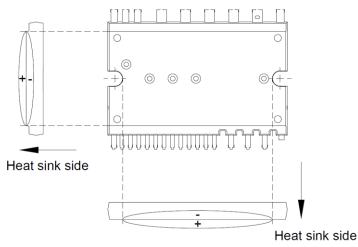


## **Mechanical Characteristics and Ratings**

Symbol	Parameter	Conditions	Min.	Тур.	Max.	Units
Mounting Torque	Mounting Screw: M3 (7)		0.59	0.69	0.78	N m
Weight			-	9.12	-	g
Flatness	Refer to Figure 6		-50	-	100	μm

#### Note:

7. Plain washers (ISO 7089-7094) are recommended.



**Figure 6. Flatness Measurement Position** 

## **Recommended Operation Conditions**

Symbol	Parameter	Conditions	Min.	Тур.	Max.	Units
V <sub>PN</sub>	Supply Voltage	Applied between P-NU, NV, NW	0	300	400	V
$V_{DD}$	Control Supply Voltage	Applied between V <sub>DD</sub> -COM	13.5	15.0	16.5	V
$V_{DB}$	High-Side Bias Voltage	Applied between $V_{B(U)}$ -U, $V_{B(V)}$ -V, $V_{B(W)}$ -W	13.5	15.0	18.5	V
$dV_{DD}/dt$ , $dV_{DB}/dt$	Control Supply Variation		-1	-	+1	V/µs
t <sub>dead</sub>	Arm Shoot-Through Blocking Time	For each input signal	1.5	-	-	μs
f <sub>PWM</sub>	PWM Input Frequency	-40°C < T <sub>J</sub> < 150°C	-	-	20	kHz
PW <sub>IN(ON)</sub>	Minimum Instant Dulle NAtional (8)		0.5	-	-	μs
PW <sub>IN(OFF)</sub>	Minimum Input Pulse Width (8)		0.5	-	-	μs
СОМ	COM Variation	Between COM-NU, NV, NW (including surge)	-5.0	-	5.0	V

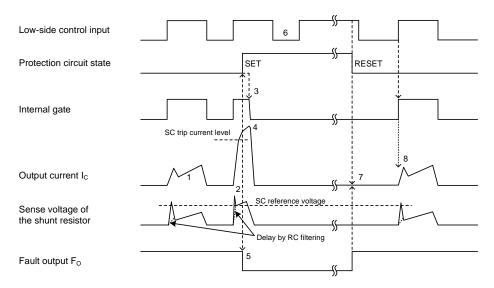
#### Note:

8. IPM may not respond if the input pulse width is less than  $\text{PW}_{\text{IN}(\text{ON})}, \text{PW}_{\text{IN}(\text{OFF})}.$ 

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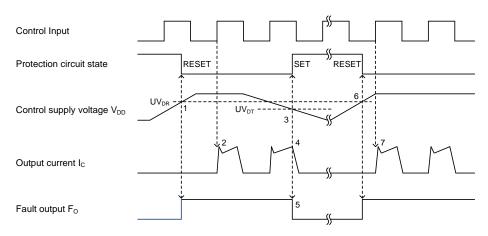


#### **Time Charts of the IPM Protective Function**



- (1) Normal operation: IGBT turns on and outputs current.
- (2) Short-circuit current detection (SC triggered).
- (3) All low-side IGBTs' gates are hard interrupted.
- (4) All low-side IGBTs turn OFF.
- (5)  $F_O$  output time ( $t_{FO}$ )=minimum 20 $\mu$ s.
- (6) Input = "L": IGBT OFF.
- (7) Fault output finishes, but output current will not turn on until next ON signal (L→H).
- (8) Normal operation: IGBT turns on and outputs current.

Figure 7. Short-Circuit Protection (Low-side Operation Only with the External Shunt Resistor and RC Filter)

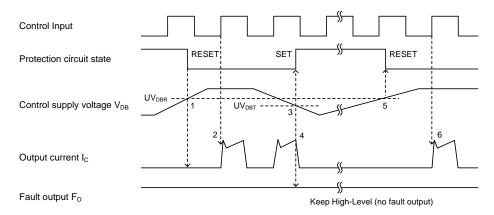


- (1) Control supply voltage V<sub>DD</sub> exceeds under voltage reset level (UV<sub>DR</sub>), but IGBT turns on by next ON signal (L→H).
- (2) Normal operation: IGBT turns on and outputs current.
- (3) V<sub>DD</sub> level drops to under voltage trip level (UV<sub>DT</sub>).
- (4) All low-side IGBTs turn OFF regardless of control input condition.
- (5)  $F_O$  output time ( $t_{FO}$ )=minimum 20 $\mu$ s, and  $F_O$  stays low as long as  $V_{DD}$  is below  $UV_{DR}$ .
- (6) V<sub>DD</sub> level reaches UV<sub>DR</sub>.
- (7) Normal operation: IGBT turns on and outputs current.

Figure 8. Under-Voltage Protection (Low-side, UV<sub>D</sub>)

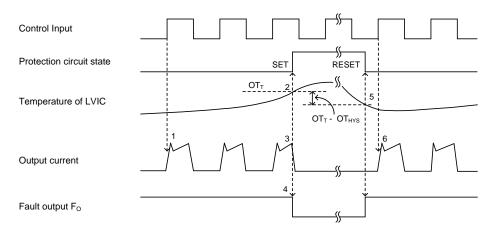
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- (1) Control supply voltage  $V_{DB}$  rises. After the voltage reaches under voltage reset level  $UV_{DBR}$ , IGBT turns on by next ON signal (L $\rightarrow$ H).
- (2) Normal operation: IGBT turns on and outputs current.
- (3) V<sub>DB</sub> level drops to under voltage trip level (UV<sub>DBT</sub>).
- (4) All high-side IGBTs turn OFF regardless of control input condition, but there is no  $F_0$  signal output.
- (5) V<sub>DB</sub> level reaches UV<sub>DBR</sub>.
- (6) Normal operation: IGBT turns on and outputs current.

Figure 9. Under-Voltage Protection (High-side, UVDB)



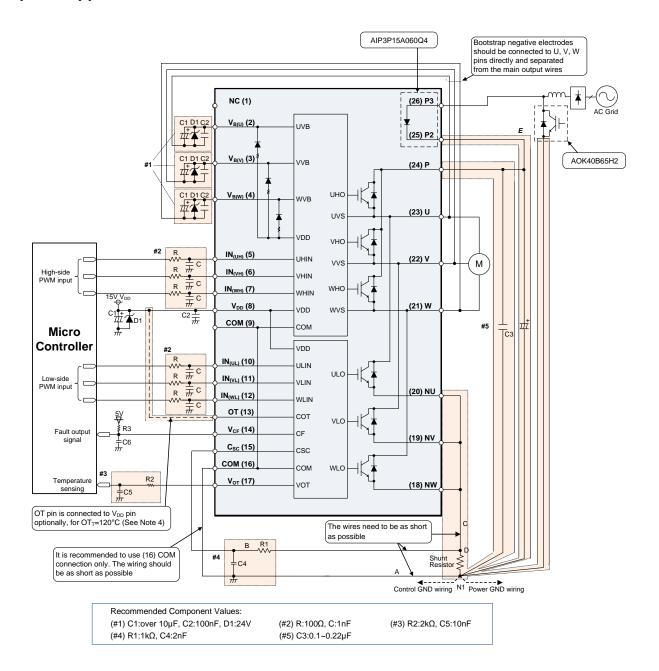
- (1) Normal operation: IGBT turns on and outputs current.
- (2) LVIC temperature exceeds over-temperature trip level (OT<sub>T</sub>).
- (3) All low-side IGBTs turn off regardless of control input condition.
- (4)  $F_0$  output time ( $t_{F0}$ )=minimum 20 $\mu$ s, and  $F_0$  stays low as long as LVIC temperature is over  $OT_T$ .
- (5) LVIC temperature drops to over-temperature reset level (OT $_{T}$ -OT $_{HYS}$ ).
- (6) Normal operation: IGBT turns on by the next ON signal  $(L\rightarrow H)$ .

Figure 10. Over-Temperature Protection (Low-side, Detecting LVIC Temperature)

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## **Example of Application Circuit**



- (1) GND pattern: The star ground design is recommended. GND pattern should be separated at the one point of the shunt resistors.
- (2) COM pin: It is recommended to only use the (16) COM pin to minimize SC detection noise. Leave pin (9) NC (No Connection).
- (3) A Zener diode D1 (24V/1W) is recommended between each pair of control supply pins to prevent surge destruction.
- (4) Snubber capacitor: The wiring between the IPM and snubber capacitor (C3) including the shunt resistors should be as short as possible.
- (5) C<sub>SC</sub> pin circuit: C4 should be placed as close to C<sub>SC</sub> pin and COM (16) pin as possible to prevent protection function errors.
- (6) P2 pin connection: The pin P2 (PFC diode cathode) should connected directly to the positive terminal of DC-link capacitor as shown in the trace E.
- (7) Bootstrap capacitors: It is recommended that all capacitors are mounted as close to the IPM as possible.
- (8) Input circuit: The R and C filter circuit should be mounted to reduce input signal noise by high speed switching. C should be placed as close to COM (16) pin as possible.
- (9) V<sub>CF</sub> pin circuit: V<sub>CF</sub> output is open drain type. The signal line should be pulled up to the positive side of the 5V/3.3V logic power supply with a proper resistor R3. For the detailed design guide, please refer to the Figure 5.

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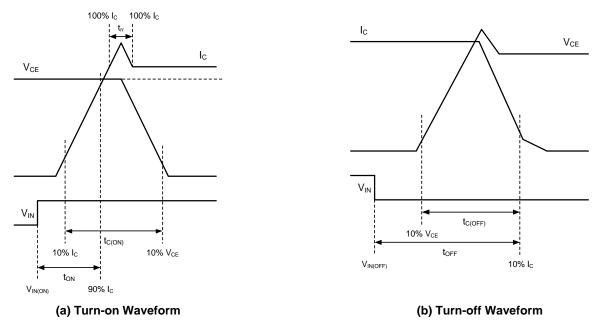
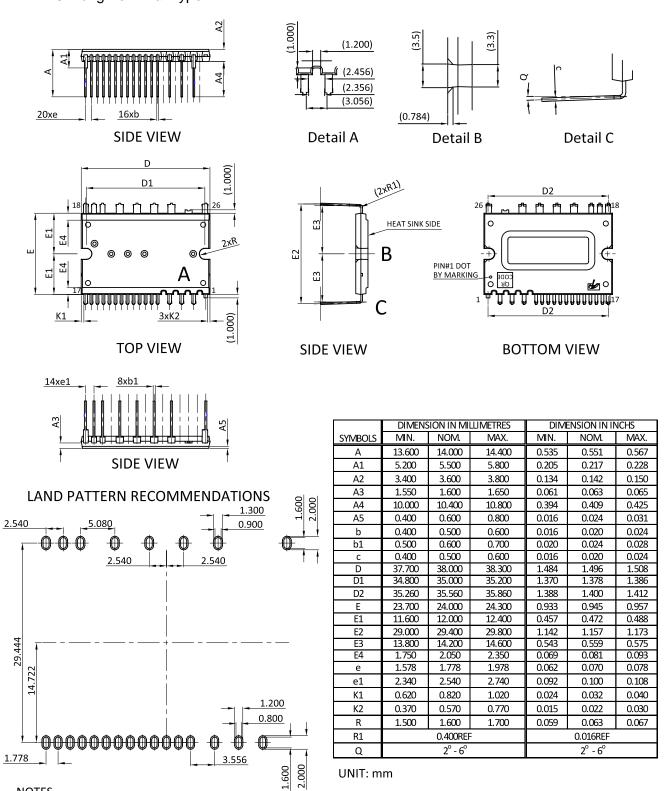


Figure 11. Switching Times Definition

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IPM-3: Long Terminal Type



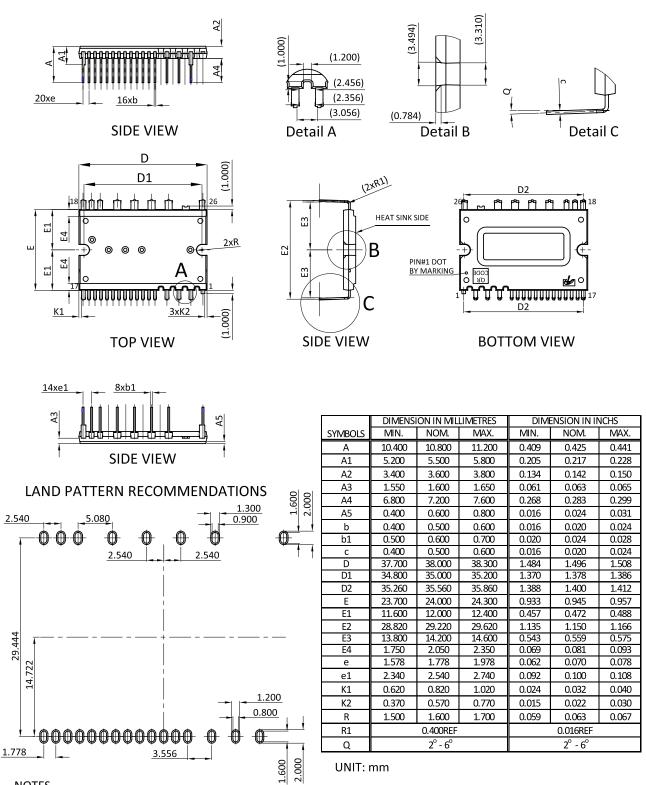
## NOTES

- 1. PACKAGE BODY SIZES EXCLUDE MOLD FLASH AND GATE BURRS, MOLD FLASH SHOULD BE LESS THAN 6 MIL.
- 2. TOLERANCE 0.100 MILLIMETERS UNLESS OTHERWISE SPECIFIED.
- 3. CONTROLLING DIMENSION IS MILLIMETER, CONVERTED INCH DIMENSIONS ARE NOT NECESSARILY EXACT.

4. () IS REFERENCE.



IPM-3A: Normal Terminal Type



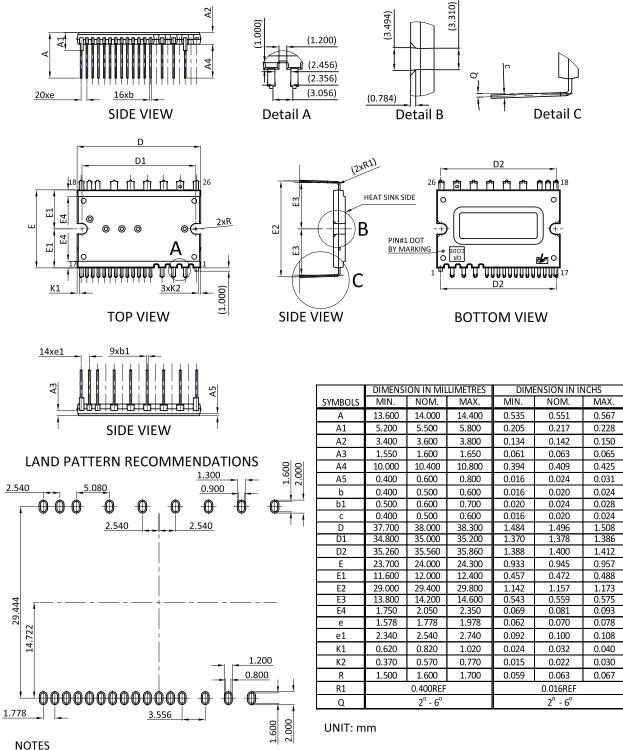
#### **NOTES**

- 1. PACKAGE BODY SIZES EXCLUDE MOLD FLASH AND GATE BURRS, MOLD FLASH SHOULD BE LESS THAN 6 MIL.
- 2. TOLERANCE 0.100 MILLIMETERS UNLESS OTHERWISE SPECIFIED.
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4. () IS REFERENCE.



IPM-3B: Long Terminal Type with PFC Diode

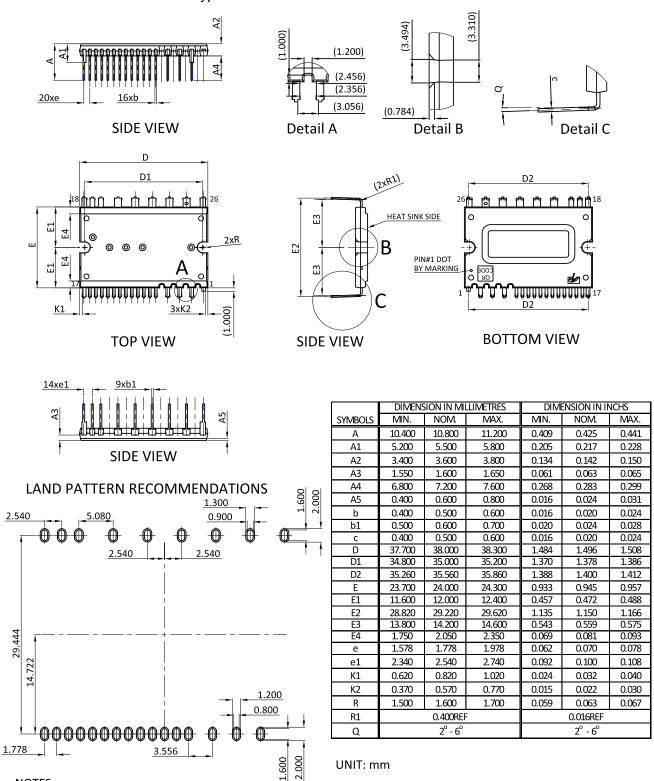


- 1. PACKAGE BODY SIZES EXCLUDE MOLD FLASH AND GATE BURRS, MOLD FLASH SHOULD BE LESS THAN 6 MIL.
- 2. TOLERANCE 0.100 MILLIMETERS UNLESS OTHERWISE SPECIFIED.
- 3. CONTROLLING DIMENSION IS MILLIMETER, CONVERTED INCH DIMENSIONS ARE NOT NECESSARILY EXACT.

4. ( ) IS REFERENCE.



IPM-3C: Normal Terminal Type with PFC Diode



- NOTES
  1. PACKAGE BODY SIZES EXCLUDE MOLD FLASH AND GATE BURRS, MOLD FLASH SHOULD BE LESS THAN 6 MIL.
- 2. TOLERANCE 0.100 MILLIMETERS UNLESS OTHERWISE SPECIFIED.
  3. CONTROLLING DIMENSION IS MILLIMETER, CONVERTED INCH DIMENSIONS ARE NOT NECESSARILY EXACT.
- 4. () IS REFERENCE.



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